BLP05H6200XR

Power LDMOS transistor

Rev. 1 — 18 May 2015

Objective data sheet

1. Product profile

1.1 General description

A 200 W extremely rugged LDMOS power transistor for broadcast and industrial applications in the HF to 600 MHz band.

Table 1. Application information

Test signal	f	V _{DS}	P _L	G p	η_D
	(MHz)	(V)	(W)	(dB)	(%)
pulsed RF	108	50	200	28	75

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 600 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	gate 2		,
2	gate 1	4 3	4
3	drain 1		
4	drain 2	pin 1 index	Y
5	source	[1]	
			3 aaa-003574

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package	Package		
	Name	Description	Version	
BLP05H6200XR	HSOP4F	plastic, heatsink small outline package; 4 leads(flat)	SOT1223-2	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	135	V
V_{GS}	gate-source voltage		-6	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1	l -	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _j = 115 °C	[1][2]	<tbd></tbd>	K/W
Z _{th(j-c)}	transient thermal impedance from junction to case	T_j = 150 °C; t_p = 100 μ s; δ = 20 %	[3]	<tbd></tbd>	K/W

- [1] T_i is the junction temperature.
- [2] $R_{th(j-c)}$ is measured under RF conditions.
- [3] See <tbd>.

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6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.0 \text{ mA}$	135	-	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 100 \text{ mA}$	1.25	1.8	2.25	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 50 \text{ mA}$	-	1.7	-	V
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	14.3	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nΑ
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.5 \text{ A}$	-	0.43	-	Ω

Table 7. AC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	0.9	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	120	-	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	39	-	pF

Table 8. RF characteristics

Test signal: pulsed RF; t_p = 100 μ s; δ = 20 %; f = 108 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 100 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 200 W	<tbd></tbd>	28	-	dB
RLin	input return loss	P _L = 200 W	-	-10	-	dB
η_{D}	drain efficiency	P _L = 200 W	<tbd></tbd>	75	-	%

7. Test information

7.1 Ruggedness in class-AB operation

The BLP05H6200XR is capable of withstanding a load mismatch corresponding to VSWR > 65 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 100 mA; P_{L} = 200 W pulsed; f = 108 MHz.

7.2 Impedance information

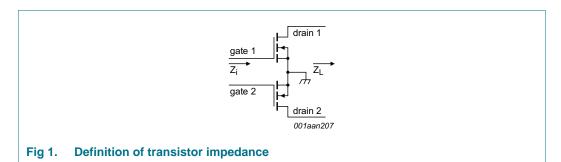


Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 50 \text{ V}$ and $P_L = 200 \text{ W}$.

f	Z _i	Z _L
(MHz)	(Ω)	(Ω)
108	<tbd></tbd>	<tbd></tbd>

7.3 UIS avalanche energy

Table 10. Typical avalanche data per section

 T_{amb} = 25 °C; typical test data; test jig without water cooling.

I _{AS}	E _{AS}
(A)	(J)
<tbd></tbd>	<tbd></tbd>
<tbd></tbd>	<tbd></tbd>
<tbd></tbd>	<tbd></tbd>

For information see application note AN10273.

8. Package outline

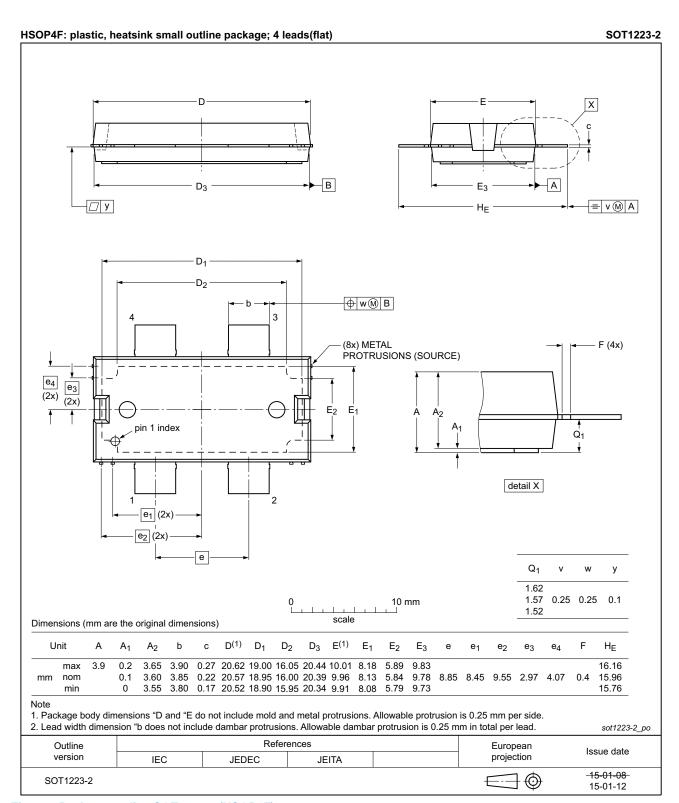


Fig 2. Package outline SOT1223-2 (HSOP4F)

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9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
SMD	Surface Mounted Device
UIS	Unclamped Inductive Switching
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP05H6200XR v.1	20150518	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Power LDMOS transistor

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